

Stretched chemical bonds in Si_6H_6 : A transition from ring currents to localized π -electrons?

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Abstract

Motivated by solid-state studies on the cleavage force in Si, and the consequent stretching of chemical bonds, we here study bond stretching in the, as yet unsynthesized, free space molecule Si_6H_6 . We address the question as to whether substantial bond stretching (but constrained to uniform scaling on all bonds) can result in a transition from ring current behaviour, characteristic say of benzene at its equilibrium geometry, to localized π -electrons on Si atoms. Some calculations are also recorded on dissociation into 6 SiH radicals. While the main studies have been carried out by unrestricted Hartree-Fock (HF) theory, the influence of electron correlation has been examined using two forms of density functional theory. Planar Si_6H_6 treated by HF is bound to be unstable, not all vibrational frequencies being real. Some buckling is then allowed, which results in real frequencies and stability. Evidence is then provided that the non-planar structure, as the Si-Si distance is increased, exhibits π -electron localization in the range 1.2–1.5 times the equilibrium distance.

Key words: bond stretching, Si_6H_6 , C_6H_6 (benzene), metal-insulator transition.

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1 Introduction

In a fairly recent study, Matthai and March [1] have used a coordination-dependent force field constructed by Tersoff [2] for crystalline Si, to calculate the cleavage force for two different cleavage planes. This led them to propose that Si-Si bonds in the diamond lattice structure have comparable elasticity to the bond in the free space H_2 molecule. Coulson and Fischer [3] made a variational calculation on H_2 , using asymmetric orbitals centred on the two protons at separation R , which showed that conventional LCAO-MO was a viable approach until R reached $1.6R_0$, with R_0 the equilibrium bond length in free space H_2 . The cleavage force calculations of Matthai and March [1] led to a slightly larger value than 1.6, characterizing the elasticity of the Si-Si bond in crystalline Si.

This has motivated us to study the stretching of Si-Si bonds in a different chemical environment, namely Si_6H_6 in free space. Of course, in this, as yet unsynthesized, molecule, the natural ‘zero-order’ hybrids are quasi- sp^2 in character, in contrast to sp^3 in the diamond lattice structure of Si. Therefore, the new feature in the bond stretching study undertaken here is the behaviour of the π -electrons, the MOs of which would conventionally be built, again in zero-order approximation, from linear combinations of $3p_z$ Si orbitals, the z axis being perpendicular to the (assumed) planar molecule, with appropriate phase factors (see, *e.g.*, Ref. [4]).

It is important to say that strain energies of silicon rings and clusters have been studied earlier by Zhao and Gimarc [5]. The work on bucky-tori by Babic *et al.* [6] is also noteworthy in the same context. Finally, the relatively weak π -bonding ability of silicon versus carbon is emphasized in the study by Baldrige *et al.* [7].

The outline of the paper is then as follows. In Sec. 2 immediately below, we record the results of a spin-compensated Hartree-Fock (HF) calculation of Si_6H_6 . This predicts a stable molecule which is already ‘bound’ at the HF level, with a substantial binding energy, even though no successful synthesis has been achieved as yet, as already mentioned.

The spin-compensated HF treatment is then extended to the study of uniformly scaled Si_6H_6 , in which Si-Si and Si-H bonds are stretched in ‘benzene-like’ geometry by a common scaling factor λ . This spin-compensated HF treatment is then compared and contrasted with a less restricted HF study in which, though a single determinantal wave function is still employed, different space orbitals are permitted for different spin directions. Though constraints are still applied (*e.g.*, the multiplicity is inserted), such spin density states eventually prove to be lower than the spin-compensated HF energy as the scale factor is increased sufficiently. Some details of the spin density are also referred to in Sec. 4 and in the Appendix for the case of benzene. Then, in Sec. 5, we have assessed the likely changes in the HF results due to electron correlation by employing density functional theory. The major conclusions of the HF studies remain intact, the binding of the molecule with respect to SiH radicals being stabilized somewhat by correlation inclusion.

2 Equilibrium geometry and uniform stretching of Si-Si and Si-H bonds by a scaling factor

2.1 Equilibrium properties from spin-compensated Hartree-Fock (HF) calculations

In this section we shall first record the results of a spin-compensated (restricted) Hartree-Fock (RHF) calculation on the equilibrium geometry of Si_6H_6 . We also anticipate results of analogous kind for C_6H_6 , to be referred to in the Appendix. All calculations were performed with the **Gaussian98** program [8] with both a 6-31G* and a cc-pVTZ basis set (for H and C atoms [9], and for Si atoms [10]). The total ground state energy E_{HF} of the single atoms and radicals (in unrestricted Hartree-Fock, UHF, approximation), and of the Si_6H_6 and C_6H_6 molecules (RHF) are recorded in Table 1, together with the equilibrium bond lengths. The binding energy relative to 6 Si and 6 H isolated atoms, as well as that relative to 6 C and 6 H isolated atoms, is also recorded.

2.2 Uniform stretching of all bonds by a common scale factor

With this as background, we turn to consider the stretching of chemical bonds in the Si_6H_6 molecule. The stretching of Si-Si bonds was referred to already in connection with the cleavage force in crystalline Si in its diamond structure. Of course, we are now considering such stretching in (a) a free space environment, and (b) in a situation in which sp^2 hybridization is replacing the basic sp^3 hybrids of the solid state (see also Stenhouse *et al.* [11] for amorphous Si and its electron density distribution). In this section, we shall confine ourselves to uniform stretching of all Si-Si and Si-H bonds in Si_6H_6 by a common scale factor λ .

Fig. 1 shows the ground-state energy E of Si_6H_6 in hartrees as a function of the uniform scaling factor λ over a wide range of λ , covering both bond stretching ($\lambda > 1$), and shortening ($\lambda < 1$). Equilibrium is achieved for $\lambda = 1$ (no stretching), corresponding to a ‘benzene-like’ (planar) geometry, for which energies and bond lengths are given in Tab. 1. The dashed line in Fig. 1 refers to the sum of atomic energies: *i.e.*, that of 6 Si and 6 H isolated atoms. Points marked by filled squares refer to a RHF calculation, whereas points marked by filled circles refer to an unrestricted Hartree-Fock (UHF) calculation, characterized by a state with a non-zero spin density, built still on a single determinantal wave function, but now allowing different space orbitals for different spin directions. All UHF curves here are with spin multiplicity $M = 1$. It is evident that the UHF result is always lower in energy than the RHF result, with the former tending to the correct dissociation limit (dashed line) as λ increases. It is found that the (putative) Si_6H_6 molecule binds for $\lambda \simeq 0.7 \div 1.3$, with a binding energy slightly lower than 1 hartree, measured relative to the dissociation limit.

Concerning the RHF curves, it turns out that as λ increases, the symmetry properties of the solution change from those near equilibrium, which is the reason of the crossing of the RHF curves near $\lambda \sim 1.3$ in Fig. 1. Specifically, while the symmetry of the HF state is a_{1g} on both branches, the symmetry of the one-electron orbitals in the HF determinant is different. Around equilibrium ($\lambda \simeq 1$) we have $[a_{2u}, e_{1g}]$ for the three highest occupied orbitals, which changes to $[b_{1u}, e_{2g}]$ when bonds are further stretched ($\lambda > 1.3$).

We shall return to the discussion of Fig. 1, when we deal with spin density in Sec. 4

below. However, we have also performed a variety of HF calculations in which only Si-Si bonds are uniformly stretched by λ , whereas Si-H bonds are fixed at their equilibrium bond lengths. The next section is devoted to comparing and contrasting the ground-state energies with those reported in the present section.

3 Uniform scaling of Si-Si bonds only, with fixed Si-H bond lengths: Dissociation into 6 Si-H radicals

In Fig. 2 we show the RHF and UHF solutions, along with the dissociation limit (dashed line, corresponding to $E = -1736.6298$ hartree), in the case where the ring geometry of the ‘benzene-like’ structure of Si_6H_6 is uniformly stretched by a factor λ , while the Si-H bond lengths are kept fixed at their equilibrium value. Naturally, as λ increases, the present case is energetically favoured with respect to the case of uniform stretching, because of the gain in chemical binding energy due to the short Si-H bonds.

First, we focus again on the HF singlet case (RHF in Fig. 2). For $\lambda \simeq 1$ (Fig. 2), the ground-state energy is approximately -1737.05 hartree. The RHF solution deviates from the UHF one more markedly than in the uniformly stretched case, and crosses over a different symmetry branch well above the dissociation limit. Following now the UHF curve, one observes that in this (albeit somewhat artificial) geometry, the system stays bounded only up to $\lambda \simeq 1.3$, namely for a smaller stretching than in the uniformly stretched case, whereas its energy exceeds the dissociation limit at about $\lambda \sim 1.5$, where it displays a weakly pronounced maximum (in the shape of an energy barrier), before decaying to the correct dissociation limit, as λ is further increased.

4 Itinerant *vs* localized π -electrons

Since there is a sense in which UHF calculations reflect electron ‘correlation’ by allowing different space orbitals for $\uparrow$ and $\downarrow$ spins, it is relevant to enquire whether we can draw any conclusions about itinerant *versus* localized behaviour of the π -electrons in Si_6H_6 . A form for comparison is of course the ‘sister’ molecule C_6H_6 . In this latter case, the diamagnetic susceptibility and properties relating to ring currents testify, from experiment, to the delocalization of the π -electrons.

In Figs. 3 and 4 we show the spin population magnitudes on the Si and H atoms of the Si_6H_6 ring, respectively, as a function of uniform stretching λ . Due to the threefold rotational symmetry of the lowest energy solution, spin populations had alternating signs on neighbouring radicals.

Within this approximation, π -electrons have their densities dominantly around the Si nuclei, with a tendency towards delocalization (ring currents) for low values of λ .

So far we have considered the structure of Si_6H_6 to be planar. However, a study of the normal modes of vibration reveals that not all the vibrational frequencies are real. This has led us to an investigation of the effect of buckling of the planar structure on these frequencies.

The minimum energy structure has been obtained by means of an optimization procedure at the UHF-Singlet level using a 6-31G* basis set. The resulting molecular geometry is highly symmetric (D_{3d} point group), similar to the cyclooctane (C_8H_{12}) geometry in

the chair conformation. In particular, the Si-Si and Si-H bond lengths are 2.218 Å and 1.47 Å, respectively, while the valence angles are 119.28° for Si-Si-Si and 119.31° for Si-Si-H. In contrast to planar 6-membered rings, in this structure only four atoms belong to a plane, say Si₁-Si₂-Si₄-Si₅, while the other two atoms, say Si₃ and Si₆, are one below and one above this plane (Fig. 5). Correspondingly, the angle between the four atoms plane with the Si₂-Si₃-Si₄ plane is 14.57°, while the angle between the four atoms plane and the Si₁-Si₆-Si₅ plane is -14.57°.

The vibrational analysis confirmed that this structure corresponds to a local minimum, with all the 30 normal modes being real. However, because of the symmetry, 10 frequencies are doubly degenerate, with a total of 20 single levels. The infrared spectrum should be quite simple, with only 3 active modes, namely, the doubly degenerate level at 2407.9 cm⁻¹, corresponding to the asymmetric stretching of the Si-H bond, the 800.5 cm⁻¹ level, corresponding to the asymmetric bending of the Si-Si-H valence angle, and the 489.9 cm⁻¹ level, corresponding to a composite motion of an *out of plane* vibration of the H atoms and of an asymmetric stretching of the Si-Si bonds.

Calculations of electronic energies have then been performed which lead to Fig. 6. This will now be discussed in some detail. The 6-31G* basis set was employed within the UHF framework.

Starting from the fully optimized structure for the UHF-singlet (a structure very similar to that of the cyclo-hexane, with a “chair”-like shape), the uniform scaling factor R/R_0 was increased from 0.8 to 1.7. At each step, only the Si-Si distance and one internal torsional angle were kept constant. This was required in order to allow a closed ring structure. All the other degrees of freedom (including those of the hydrogen atoms) were optimized by the calculation. The fully optimized UHF-singlet structure has been used also for the UHF-7 calculations, for which the same procedure was employed: fixed Si-Si distance plus one internal angle, all the rest was left free to be optimized, including the hydrogen variables. As can be seen from Fig. 6, up to $R/R_0 = 1.15$, the UHF-1 is more stable than the UHF-7. Such a situation corresponds to having the electrons localized on each Si *p*-orbital. From $R/R_0 = 1.15$ on, the UHF-7 structures are more stable than the corresponding UHF-1, and the energy (correctly) tends to that of 6 SiH radicals, each in a doublet configuration.

The conclusion is that, in this basis, the π system localizes at a distance equal to 1.2–1.5 times the equilibrium distance. As far as the spin population is concerned, in all the UHF-1 calculations, the Gaussian program assigns the value 0 to every atom in the molecule. On the other hand, positive values, with moduli about unity, are found at the end of each calculation for the UHF-7 configurations.

5 Summary and future directions

We have here presented a variety of HF calculations for stretched chemical bonds in the, as yet unsynthesized, molecule Si₆H₆. The UHF state is lower in energy than the HF singlet state with uniform scaling of all bonds by a factor λ , throughout the range of λ investigated in the present work ($\lambda \simeq 0.8$ to 2.6), and a non zero spin density is predicted on Si (and H) nuclei, with alternating sign on neighbouring radicals.

In Sec. 4 above, we have shown that, in contrast of course to benzene, the stable form

predicted for Si_6H_6 at the present level of approximation is a non-planar structure. The motivation for this was that the planar structure we initially investigated was ‘unstable’ in the sense that not all the vibrational frequencies were real. The ‘buckled’ structure reported in Sec. 4 has all its vibrational frequencies real.

Also, based on Fig. 6, we have presented evidence that for such a non-planar structure the π -electron assembly exhibits a tendency to pass from delocalized character at the equilibrium Si–Si length to localized behaviour when the bonds are stretched, the effect securing at a distance equal to 1.2 to 1.5 times the equilibrium distance.

Of course, for the future, it remains of considerable interest to see whether Si_6H_6 can be successfully synthesized. From solid-state facts, however, Si seems not to ‘like’ sp^2 hybridization, there being only diamond structure in the crystalline state, with no analogue of sp^2 bonded graphite layers with C-bonding. Nevertheless, the binding energy we have predicted relative to 6 SiH radicals is substantial ($\sim \frac{1}{2}$ hartree) and we could anticipate, from our earlier arguments [12] relating electron correlation in bonds to bond order, that electron correlation would increase this binding energy. This has been supported by the density functional results of Sec. 5.

Appendix A: Comparison with benzene with stretched bonds

To compare and contrast with the calculations reported in the main text, we summarize here results on benzene (C_6H_6) with stretched bonds. Fig. A.1 shows the ground state energy as a function of uniform scale factor λ . Clearly, the spin density HF solution rapidly becomes lower in energy than the RHF curve.

The evaluated spin densities on a C atom and on an H atom are shown in Fig. A.2. One presumes that, quite rapidly, there will be a transition in benzene from ring currents in the π -system to localized π electrons. Fig. A.3 shows the variation of the average value of the spin operator $\mathbf{S}^2$ with stretching parameter λ .

Some calculations have also been performed with dissociation into 6 independent CH radicals. The results resemble those reported in Section 3 of the main text for Si_6H_6 . However, the UHF curve on Fig. A.4 is always below the dissociation limit (compare with Fig. 2), and the spin population on a CH independent radical is 3 parallel spins (see Fig. A.5), whereas for a SiH radical one net spin is found to be more stable.

Appendix B: Approximate inclusion of electron correlation: density functional results

Having established the predictions of the unrestricted Hartree-Fock theory, among which the most significant for comparison with density functional predictions reported below are (i) a Si–Si bond length in Si_6H_6 at equilibrium of 2.214 Å and (ii) a binding energy of 0.40 a.u. with respect to SiH radicals, we turn to density functional results as a means to make an approximate assessment of the effect of electron-electron Coulombic correlations.

The BLYP (Becke [13], Lee-Yang-Parr [14]) and the B3LYP (Becke [15], Lee-Yang-Parr [14]) density functional calculations are reported in Table B.1. In contrast to the Hartree-Fock calculations, where the optimized SiH bond length for the ring was used

throughout, the Si–H distance has now been optimized separately for radicals as well as for the ring. The Si–Si bond length was optimized for the ring while it was constrained to a planar hexagon geometry.

For B3LYP, the Si–Si equilibrium bond length was found to be very close to the HF value of 2.214 Å, namely 2.215 Å. For the BLYP functional, the bond was somewhat longer (by 0.02 Å). The shorter bond length given by the B3LYP functional led to a somewhat greater binding energy ΔE with respect to the SiH radicals (bound with respect to atomization). However, both functionals are embraced by $\Delta E = 0.547 \pm 0.005$ a.u., which exceeds the HF prediction by approximately 4 eV. Correlation inclusion therefore does not change the essence of the HF results for the molecule Si₆H₆.

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Table 1

Data for equilibrium configuration (uniform stretching parameter $\lambda = 1$) of isolated Si, H, and C atoms, of SiH and CH isolated radicals, and of both Si₆H₆ and C₆H₆ molecules. M is the spin multiplicity; E_{HF} is the Hartree-Fock ground state energy. The total energy relative to 6 Si and 6 H isolated atoms equals $E_{\text{HF}}^0(6 \text{ Si} + 6 \text{ H}) = -1736.13726$, whereas that for 6 SiH isolated radicals equals $E_{\text{HF}}^0(6 \text{ SiH}) = -1736.6298$. Analogously, $E_{\text{HF}}^0(6 \text{ C} + 6 \text{ H}) = -229.14828$ and $E_{\text{HF}}^0(6 \text{ CH}) = -229.73574$. All energies and lengths are in hartrees and angstroms, respectively.

		M	E_{HF}	Spin population	Bond length
UHF	Si	3	-288.8564	2	
UHF	SiH	2	-289.4383	1.025 (Si) -0.025 (H)	1.4727 (Si-H)
RHF	Si ₆ H ₆	1	-1737.035		1.4727 (Si-H) 2.2138 (Si-Si)
UHF	C	3	-37.69157	2	
UHF	H	2	-0.499810	1	
	CH	4	-38.28929	2.940 (C) 0.060 (H)	1.0734 (C-H)
RHF	C ₆ H ₆	1	-230.7805		1.0734 (C-H) 1.3827 (C-C)

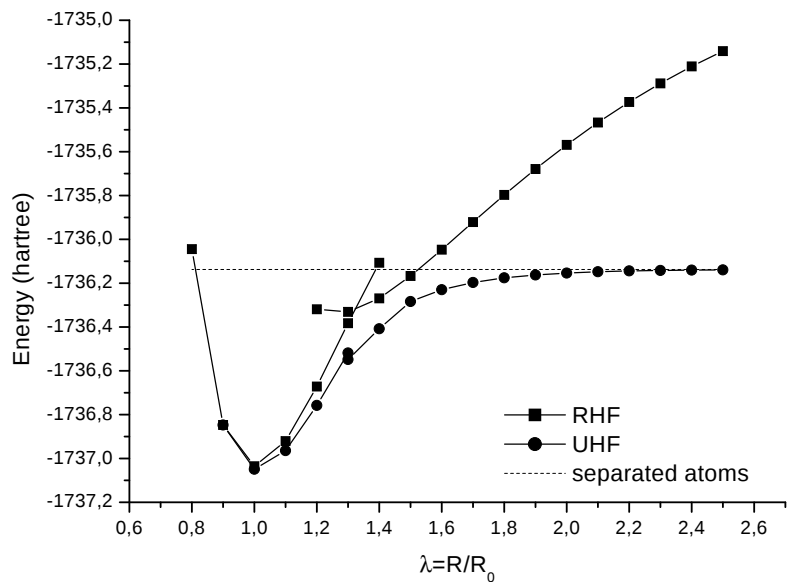


Fig. 1. Restricted (RHF) and unrestricted (UHF) Hartree-Fock potential energy curves of Si_6H_6 as a function of uniform scaling factor λ .

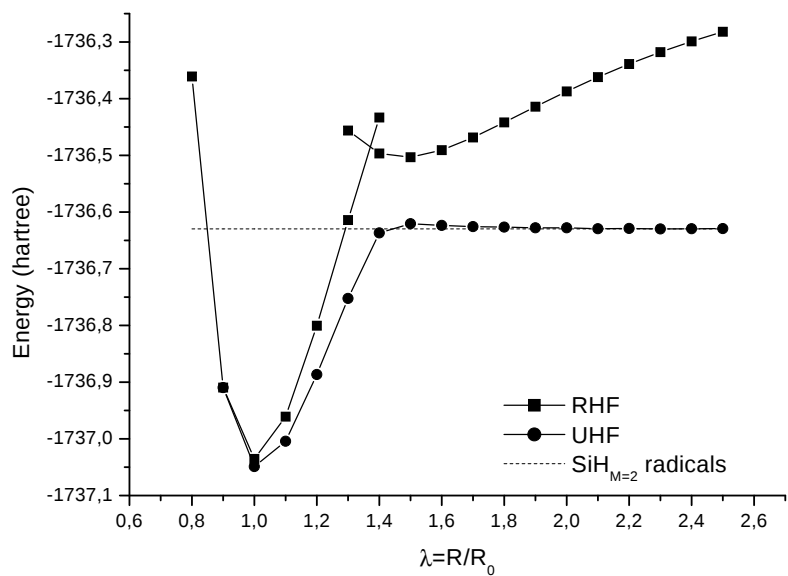


Fig. 2. Restricted and unrestricted Hartree-Fock potential energy curves of Si_6H_6 . Ring geometry of Si is scaled with λ , whereas Si-H bond lengths are kept fixed.

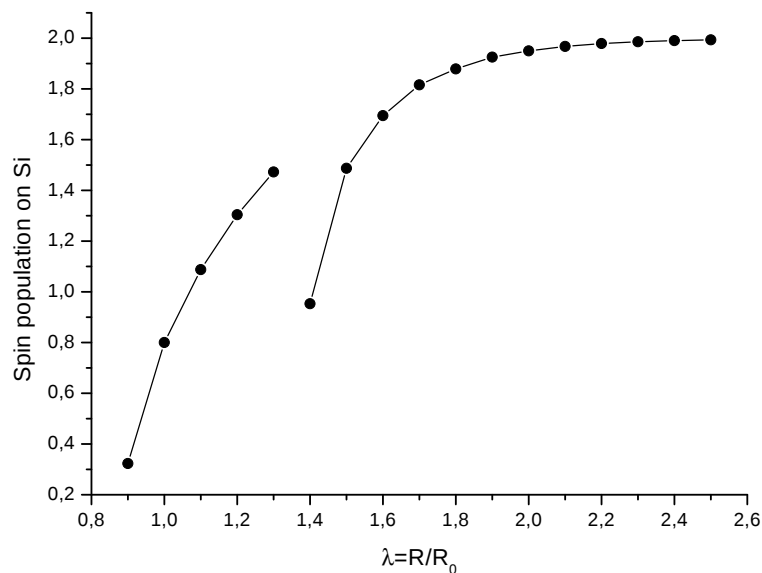


Fig. 3. Spin population magnitude on a Si atom in a Si_6H_6 ring as a function of the uniform scaling factor λ . Due to the symmetry of the UHF solution, spin populations have alternating signs on neighbouring Si atoms.

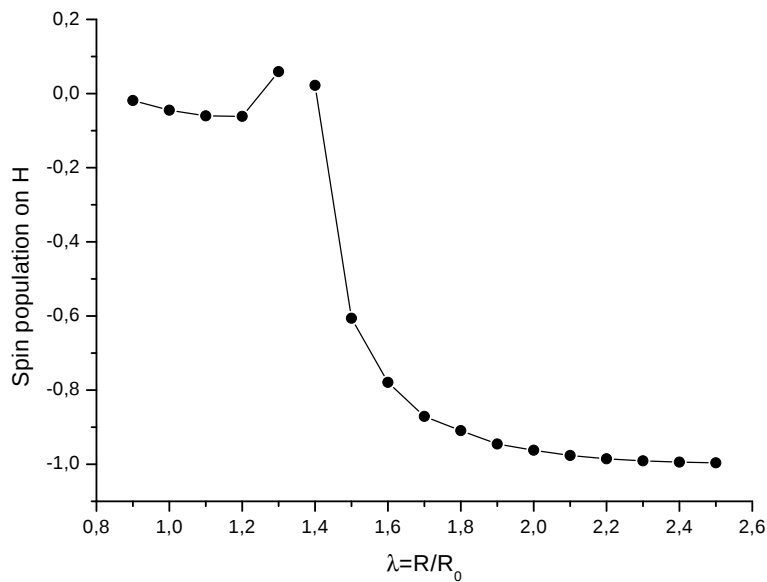


Fig. 4. Spin population on an H atom in a Si_6H_6 ring as a function of the uniform scaling factor λ . The sign is relative to that of the spin population on the Si atom belonging to the same radical (Fig. 3).

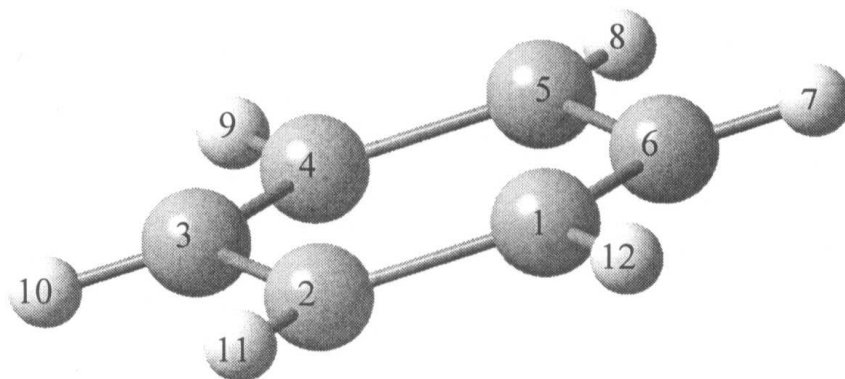


Fig. 5. Optimized structure of Si_6H_6 . See main text for discussion.

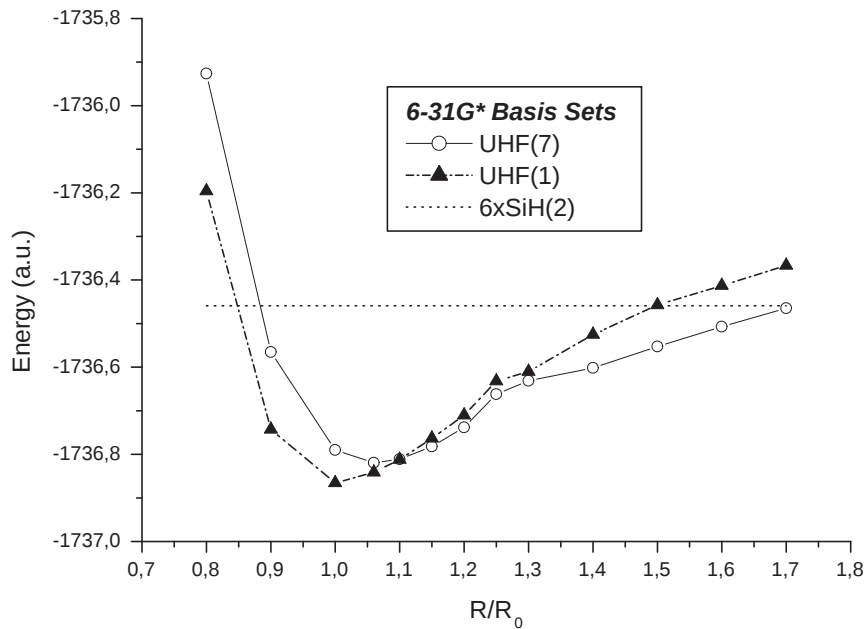


Fig. 6. Unrestricted Hartree-Fock (UHF) potential energy curves of Si_6H_6 , as a function of the uniform scaling factor $\lambda = R/R_0$, for the 6-31G* basis set. See main text for discussion.

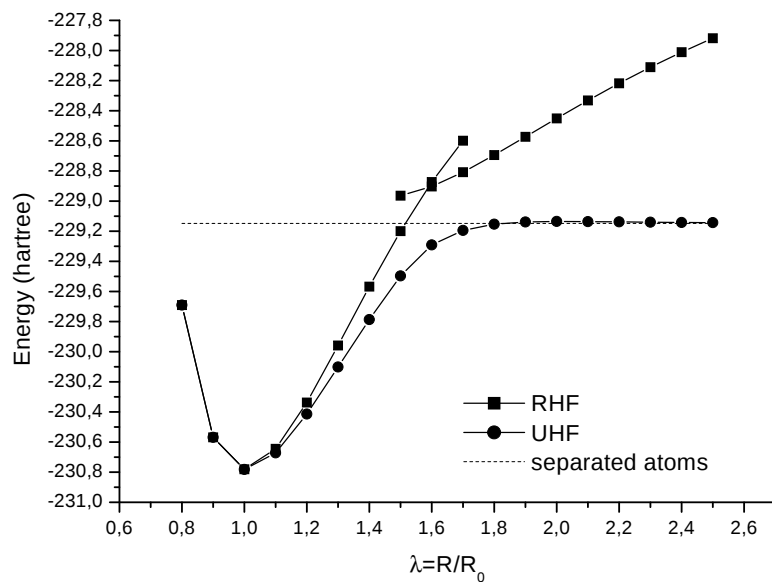


Fig. A.1. Restricted and unrestricted Hartree-Fock potential energy curves of C_6H_6 as a function of uniform scaling factor λ .

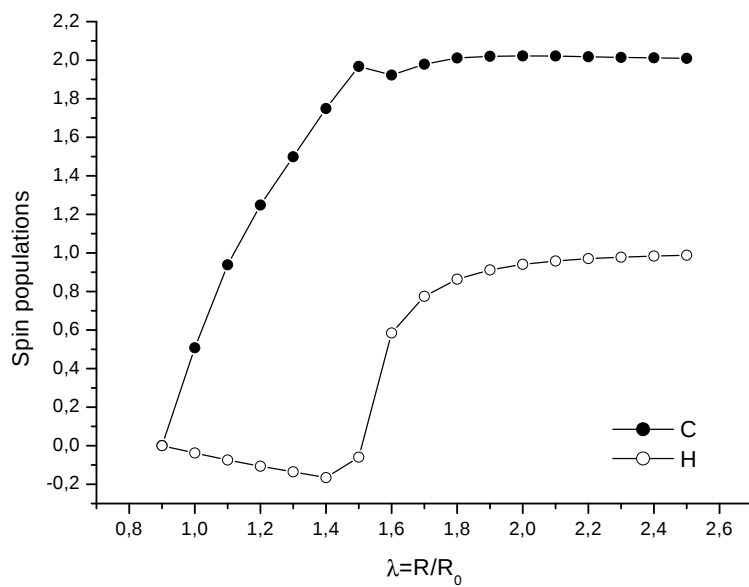


Fig. A.2. Spin population on a C atom and the corresponding H atoms in a C_6H_6 ring as a function of the uniform scaling factor λ .

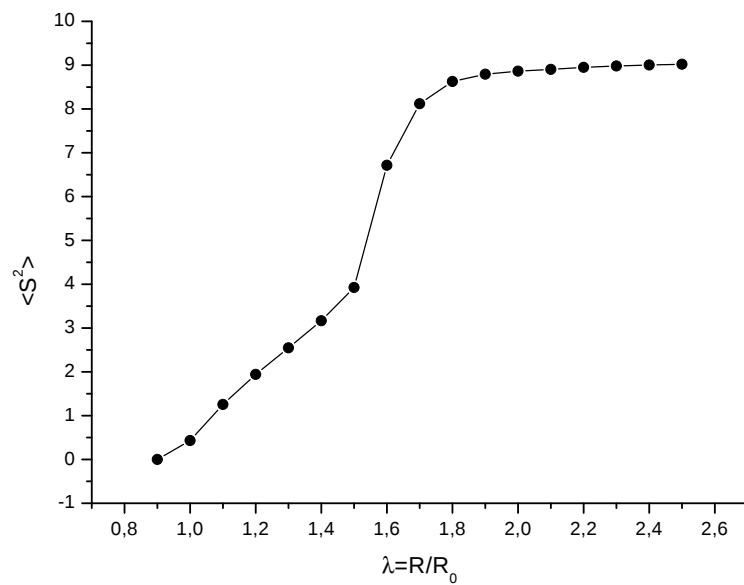


Fig. A.3. Variation of the total spin expectation value $\langle S^2 \rangle$ for the uniformly scaled benzene ring.

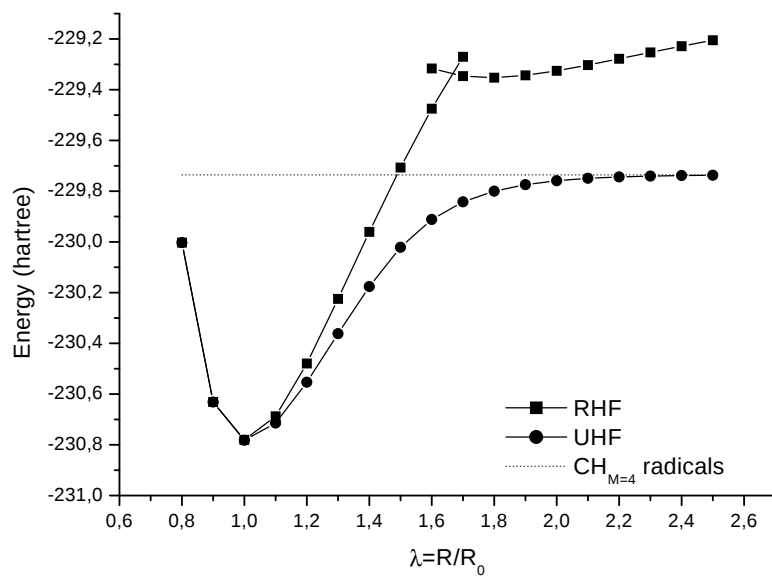


Fig. A.4. Restricted and unrestricted Hartree-Fock potential energy curves for C_6H_6 . Carbon ring geometry is scaled with λ , whereas C-H bond lengths are fixed at their equilibrium value.

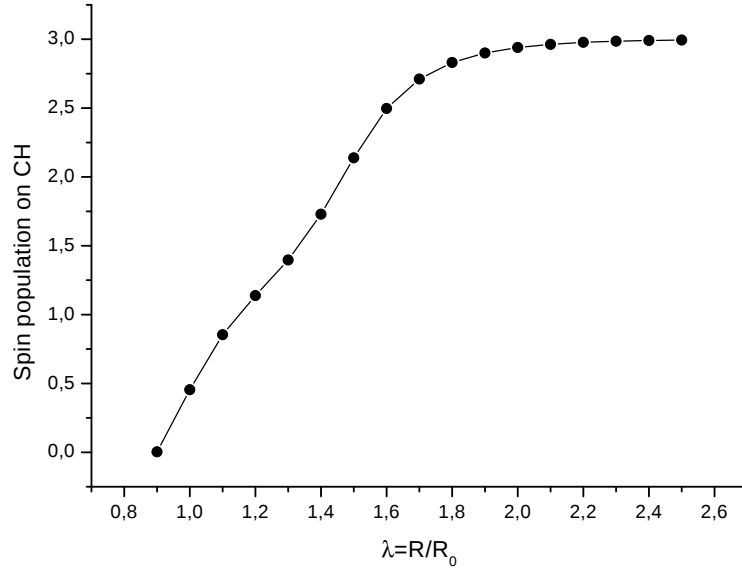


Fig. A.5. Spin population on a CH group in a C_6H_6 ring as a function of the ring diameter scaling factor.

Table B.1

Ground state energy and Si–Si and Si–H bond lengths: effect of approximate inclusion of electron correlation using two forms of density functional theory. Binding energy ΔE is related to the dissociation of Si_6H_6 into 6 SiH radicals. All energies and lengths are in hartrees and angstroms, respectively.

		SiH radical	Si_6H_6	ΔE
BLYP	Energy	–290.00	–1740.52	0.54
	Geometry	1.545 (Si–H)	1.489 (Si–H)	
			2.231 (Si–Si)	
B3LYP	Energy	–290.02	–1740.66	0.55
	Geometry	1.533 (Si–H)	1.481 (Si–H)	
			2.215 (Si–Si)	
UHF	Energy	–289.44	–1737.04	0.40
	Geometry	1.519 (Si–H)	1.473 (Si–H)	
			2.214 (Si–Si)	